THYRISTOR MODULE

PK(PD,PE)200HB

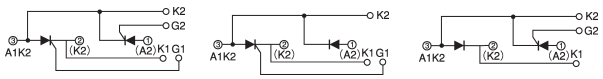
UL;E76102 (M)

Power Thyristor/Diode Module **PK200HB** series are designed for various rectifier circuits and power controls. For your circuit application. following internal connections and wide voltage ratings up to 1,600V are available.

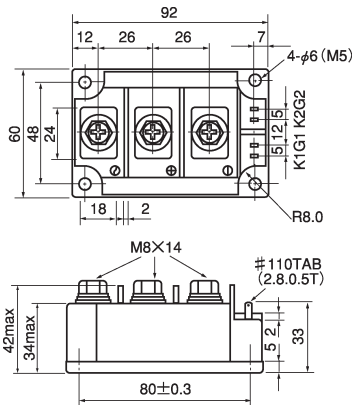
Isolated mounting base
- $I_{T(AV)}$ 200A, $I_{T(RMS)}$ 310A, I_{TSM} 5500A
- di/dt 200 A/ μs
- dv/dt 500V/ μs

(**Applications**)
Various rectifiers
AC/DC motor drives
Heater controls
Light dimmers
Static switches

Internal Configurations



PK PD PE



Unit : mm

■Maximum Ratings

Symbol	Item	Ratings		Unit
		PK200HB120 PD200HB120 PE200HB120	PK200HB160 PD200HB160 PE200HB160	
V_{RRM}	＊Repetitive Peak Reverse Voltage	1200	1600	V
V_{RSM}	＊Non-Repetitive Peak Reverse Voltage	1300	1700	V
V_{DRM}	Repetitive Peak Off-State Voltage	1200	1600	V

Symbol	Item		Conditions	Ratings	Unit
$I_{T(AV)}$	＊Average On-State Current		Single phase, half wave, 180˚conduction, Tc：74℃	200	A
$I_{T(RMS)}$	＊R.M.S. On-State Current		Single phase, half wave, 180˚conduction, Tc：74℃	310	A
I_{TSM}	＊Surge On-State Current		1/2cycle, 50Hz/60Hz, peak Value, non-reqetitive	5000/5500	A
I^2t	＊I^2t		Value for one cycle of surge current	125000	A^2S
P_{GM}	Peak Gate Power Dissipation			10	W
$P_{G(AV)}$	Average Gate Power Dissipation			3	W
I_{FGM}	Peak Gate Current			3	A
V_{FGM}	Peak Gate Voltage (Forward)			10	V
V_{RGM}	Peak Gate Voltage (Reverse)			5	V
di/dt	Critical Rate of Rise of On-State Current		I_G=100mA, Tj=25℃, V_D=1/2V_{DRM}, dI_G/dt=0.1A/μs	200	A/μs
V_{ISO}	＊Isolation Breakdown Voltage (R.M.S.)		A.C. 1 minute	2500	V
Tj	＊Operating Junction Temperature			−40～+125	℃
Tstg	＊Storage Temperature			−40～+125	℃
	Mounting Torque	Mounting (M5)	Recommended Value 1.5～2.5 (15～25)	2.7 (28)	N・m (kgf・cm)
		Terminal (M8)	Recommended Value 8.8～10 (90～105)	11 (115)	
	Mass		Typical Value	510	g

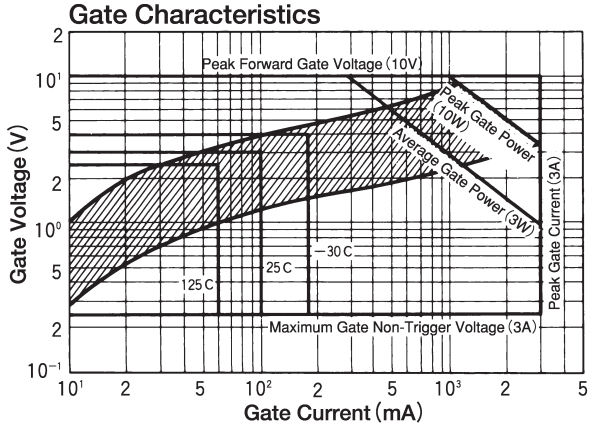
■Electrical Characteristics

Symbol	Item	Conditions	Ratings	Unit
I_{DRM}	Repetitive Peak Off-State Current, max.	at V_{DRM}, Single phase, half wave, Tj=125℃	50	mA
I_{RRM}	＊Repetitive Peak Reverse Current, max.	at V_{DRM}, Single phase, half wave, Tj=125℃	50	mA
V_{TM}	＊Peak On-State Voltage, max.	On-State Current 750A, Tj=125℃ Inst. measurement	1.50	V
I_{GT}/V_{GT}	Gate Trigger Current/Voltage, max.	Tj=25℃, I_T=1A, V_D=6V	100/3	mA/V
V_{GD}	Non-Trigger Gate, Voltage. min.	Tj=125℃, V_D=1/2V_{DRM}	0.25	V
tgt	Turn On Time, max.	I_T=250A, I_G=100mA, Tj=25℃, V_D=1/2V_{DRM}, dI_G/dt=0.1A/μs	10	μs
dv/dt	Critical Rate of Rise of Off-State Voltage, min.	Tj=125℃, V_D=2/3V_{DRM}, Exponential wave.	500	V/μs
I_H	Holding Current, typ.	Tj=25℃	50	mA
I_L	Lutching Current, typ.	Tj=25℃	100	mA
Rth(j-c)	＊Thermal Impedance, max.	Junction to case	0.18	℃/W

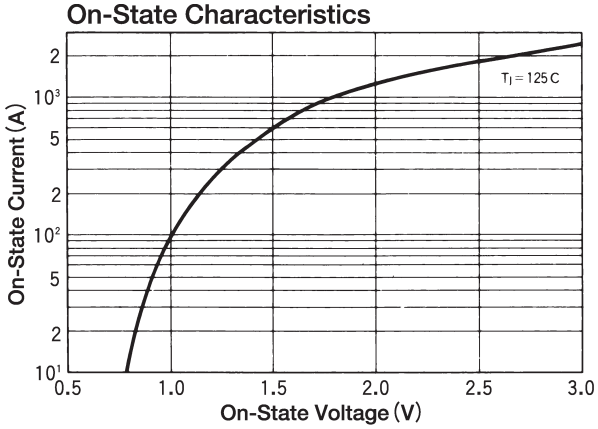
＊mark：Thyristor and Diode part. No mark：Thyristor part

SanRex

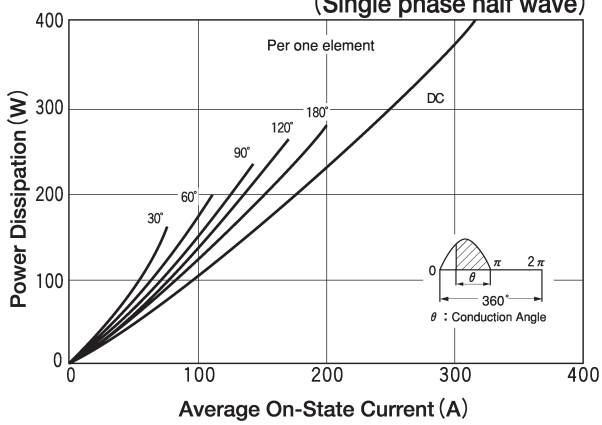
Gate Characteristics



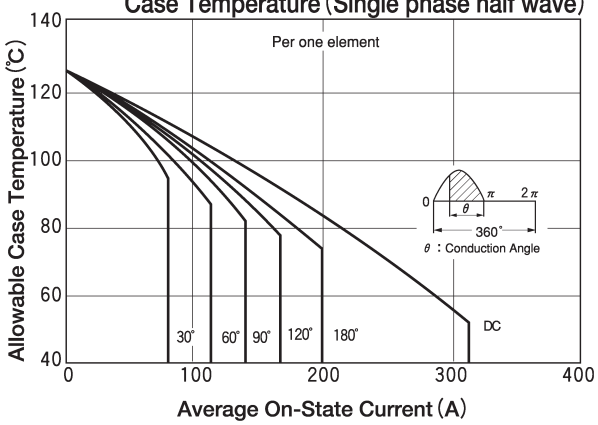
On-State Characteristics



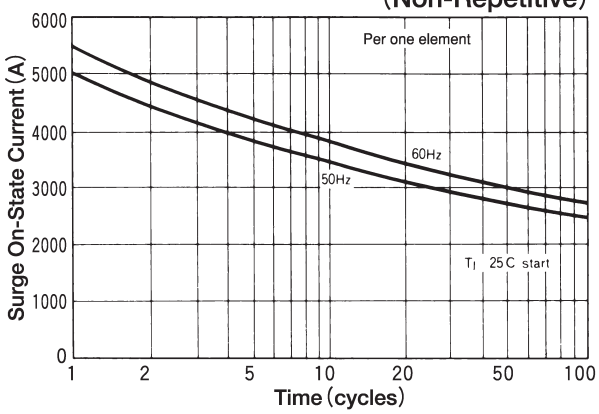
Average On-State Current Vs Power Dissipation (Single phase half wave)



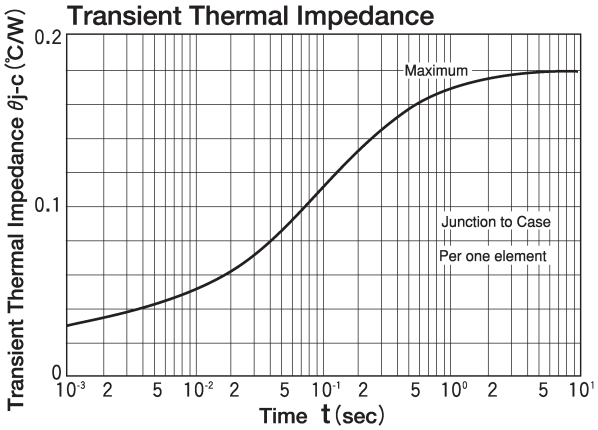
Average On-State Current Vs Maximum Allowable Case Temperature (Single phase half wave)



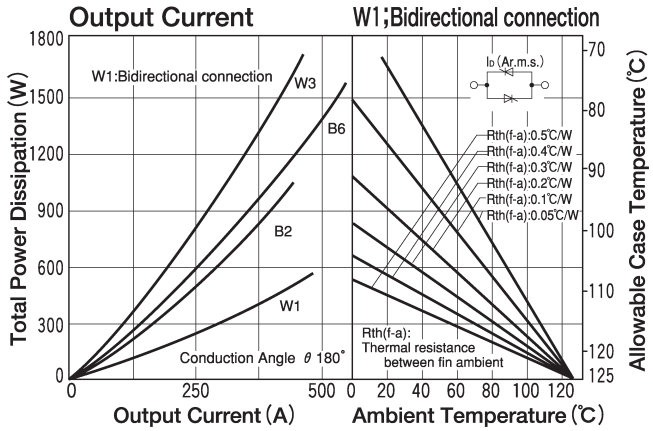
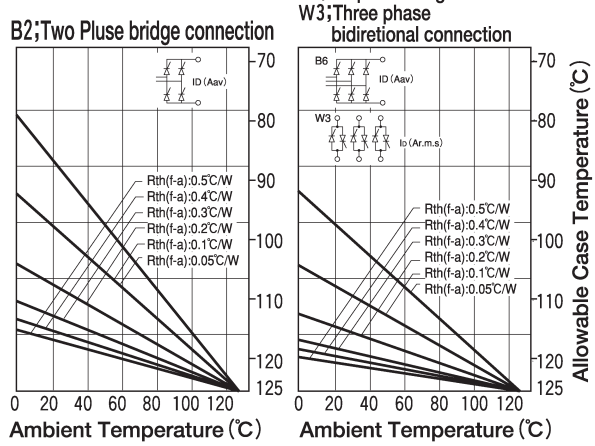
Surge On-State Current Rating (Non-Repetitive)



Transient Thermal Impedance



Output Current — W1;Bidirectional connection



B2;Two Pluse bridge connection / B6;Six pulse bridge connection / W3;Three phase bidiretional connection